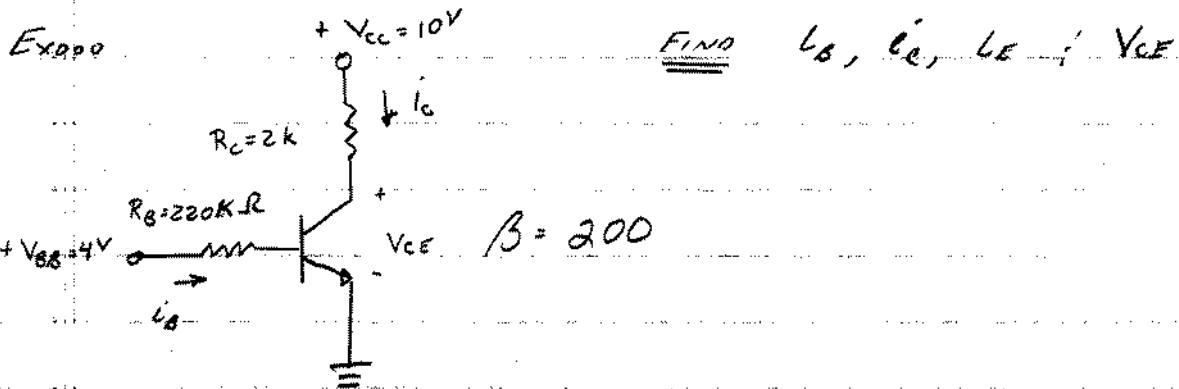
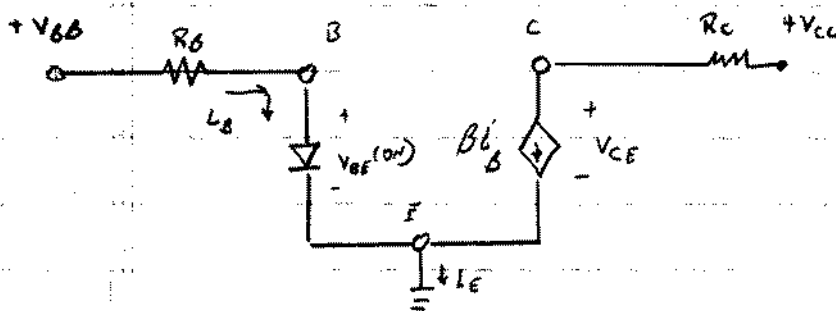


IV D.C. ANALYSIS : LOAD LINES

A. THE COMMON EMITTER CIRCUIT



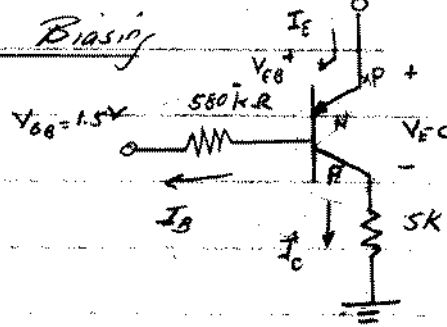
DC Piecewise Linear Model



- ① $V_{BE} = 0.7V$
- ② $I_B = \frac{4 - 0.7}{220k\Omega} = 15\mu A$
- ③ $I_C = \beta I_B = (200)(15\mu A) = 3mA$
- ④ $I_E = (1 + \beta) I_B = 3.02mA$

- ⑤ $V_{CE} = V_{CC} - I_C R_C = 10 - (3)(2) = 4V$

Note: Since $V_{BB} > V_{BE(on)}$; $V_{CE} > V_{CE(sat)}$ \Rightarrow FWO Active Mode

PNP BiasingFind I_B, I_C, I_E, V_{EC}

$$V_{EB} = 0.6$$

$$\beta = 100$$

$$\textcircled{1} \text{ KVL: } +5 + V_{EB} - I_B (580k) + 1.5 = 0$$

$$I_B = \frac{5 - 0.6 - 1.5}{580k} = 5 \mu A$$

$$\textcircled{2} \quad I_C = \beta I_B = 0.5 \text{ mA}$$

$$\textcircled{3} \quad I_E = (\beta + 1) I_B = 0.505 \text{ mA}$$

$$\textcircled{4} \text{ KVL: } -5V + V_{EC} + I_C 5k = 0 \Rightarrow V_{EC} = 5 + (.5)(5) = 2.5V$$

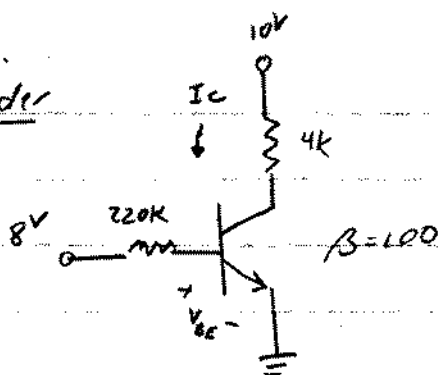
Note: ① The E-B junction is forward biased since $V_{EC} - V_{EB} > 0.6V$

② The C-B junction is reverse biased since $V_{EB} (\text{open})$

$$V_{BC} = \underset{\uparrow V_B}{(5 - 0.7)} - \underset{\uparrow V_C}{(1.5 + 5)} = 4.3 - 2.5 = 2.8$$

∴ This transistor is in Linear Active mode

$$\text{also: } V_{EC} = 2.5V > V_{EC(ON)} \checkmark$$

Consider

$$\textcircled{1} I_B = \frac{8 - 0.7}{220k} = 33.2 \mu A$$

$$\textcircled{2} I_C = \beta I_B = 3.32 \text{ mA}$$

$$\textcircled{3} V_{CE} = V_{CC} - I_C R_C = 10 - 3.32(4) = -3.28 \text{ V}$$

↑
CAN'T BE

CAN'T have neg V_{CE} in Common Emitter NPN. (see characteristic curve)

∴ Transistor is not in Active Region

$$\therefore I_C \neq \beta I_B$$

So: Sat. $V_{CE} = V_{CE}(\text{SAT}) = 0.2 \text{ V}$ ← typical

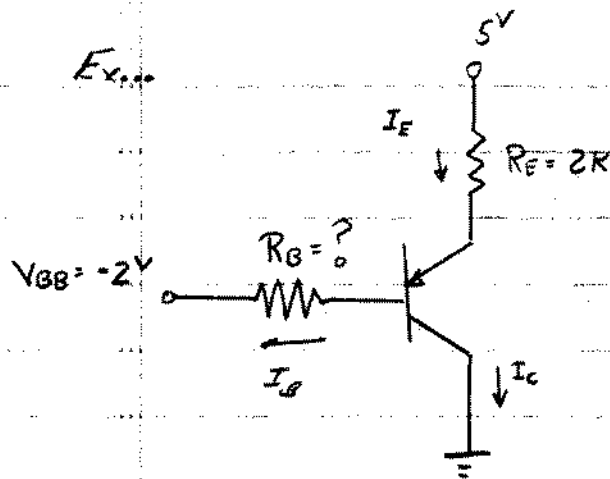
then: $I_C = I_C(\text{SAT}) = \frac{V_{CC} - V_{CE}(\text{SAT})}{R_C} = \frac{10 - 0.2}{4k} = 2.45 \text{ mA}$

and $I_E = I_B + I_C = 33.2 \mu A + 2.45 \text{ mA} = \underline{2.48 \text{ mA}}$

Notes: ① Typically $V_{CE}(\text{SAT}) = \text{constant}$ and is given, this is another piecewise linear approx of the transistor characteristic

② $I_C / I_B = \frac{2.45}{0.0332} = 74 < \beta$ which is typical of saturation.

So if $I_C < \beta I_B$ the transistor is in saturation.



Given: $V_{EB(ON)} = 0.6V$

$\beta = 60$

Find: R_B so $V_{ECQ} = 2.5V$

1. EC Loop KVL: $-5V + I_E 2k + V_{EC} = 0$

$$I_E = \frac{5 - 2.5}{2k} = \underline{1.25 \text{ mA}}$$

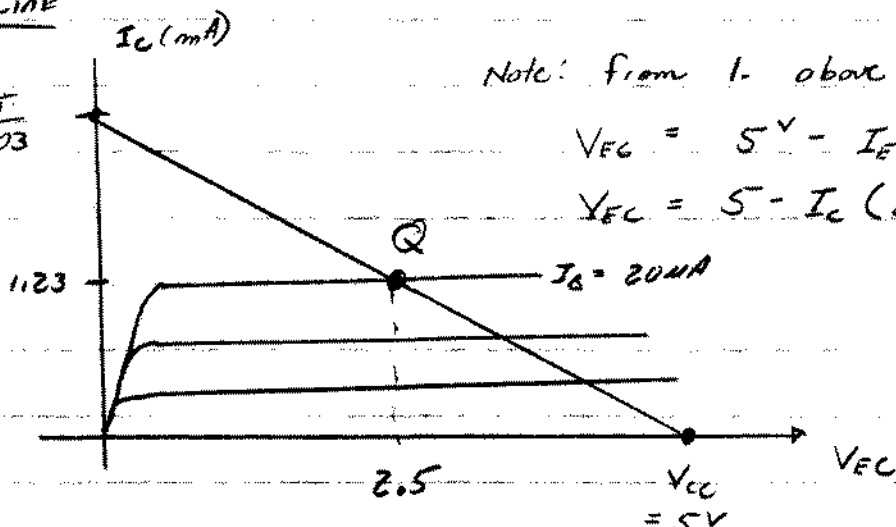
2. $I_C = \frac{\beta}{1+\beta} I_E = \left(\frac{60}{61}\right) 1.25 = \underline{1.23 \text{ mA}}$

3. $I_B = \frac{I_E}{(1+\beta)} = \underline{0.02 \text{ mA}}$

4. EB Loop KVL: $-5 + I_E 2k + V_{EB(ON)} + I_B R_B - 2 = 0$

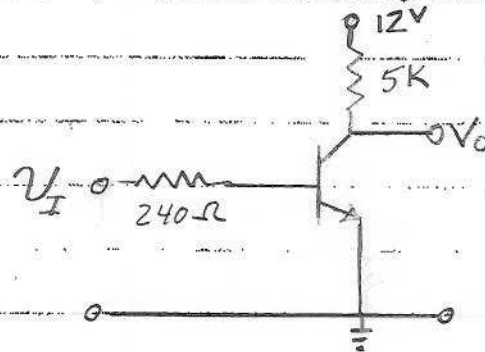
$$R_B = \frac{7 - 0.6 - 1.25(2)}{0.02 \text{ mA}} = \boxed{190k\Omega}$$

Load Line



$$2.46 \text{ mA} = \frac{5}{2.03}$$

Ex...

Given: $R_B = 240\Omega$ $V_{CC} = 12V$ $V_{BE(ON)} = 0.7V$ $V_{CE(SAT)} = 0.1$ $\beta = 75$ $R_C = 5\Omega$ Find: currents, V_o , power dissipated① $V_I = 0$: transistor is C-O, $I_B = I_C = 0$, $V_o = V_{CC} = 12V$ ② $V_I = 12V$: $I_B = \frac{V_I - V_{BE(ON)}}{R_B} = \frac{12 - 0.7}{240} = 47.1 \text{ mA}$

Assuming Saturation:

$$I_C = \frac{V_{CC} - V_{CE(SAT)}}{R_C} = \frac{12 - 0.1}{5} = 2.38A$$

$$\text{c.k.: } \frac{I_C}{I_B} < \beta$$

$$\frac{2.38}{0.0471} = 50.6 < \beta \checkmark$$

↑
Large for most
transistors. Would need
a power transistor

$$V_o = V_{CE(SAT)} = 0.1V$$

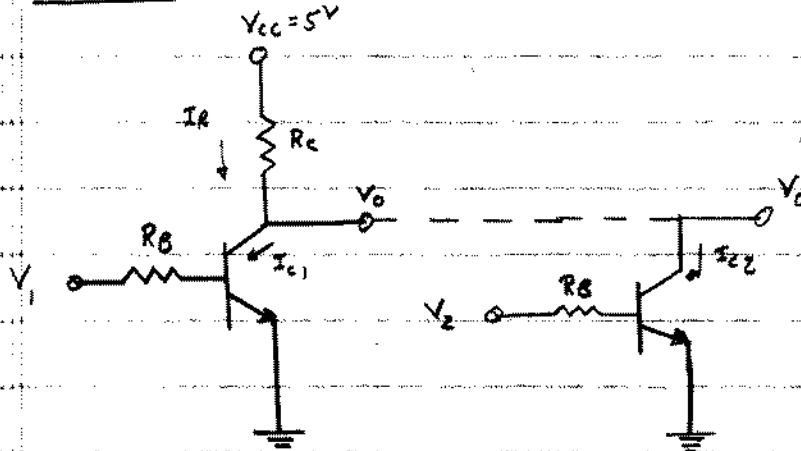
③ power dissipated in transistor = $P = I_C V_{CE} + I_B V_{BE}$

$$= (2.38)(0.1) + (0.0471)(0.7)$$

$$= \underline{\underline{0.271W}}$$

B. Digital Logic

Consider



For $V_1 = 0$, $Q1$ is cutoff, $I_B = 0$, $I_C = 0$, $V_0 = V_{CC} = 5V$

For $V_1 = 5V$, $Q1$ is SATURATED, $V_0 = V_{CE} \approx 0.2V$

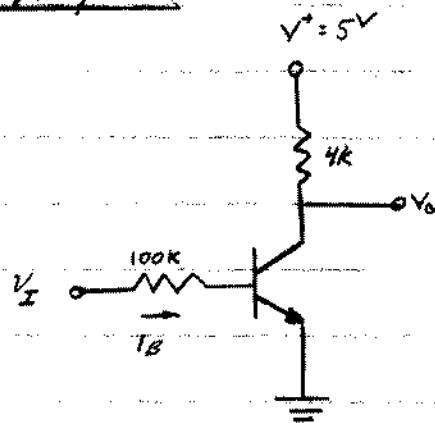
Now add a second transistor: 2 input NOR GATE

V_1	V_2	V_0
0	0	5V
5	0	0.2V
0	5	0.2
5	5	0.2

Ex 000 $\beta = 50$, $V_{BE(ON)} = 0.7V$, $V_{CE(SAT)} = 0.2V$

$R_E = 1K$, $R_B = 20K$

V_1	V_2	V_0	I_R	Q_1	Q_2
0	0	5	0	$I_{B1} = I_{C1} = 0$	$I_{B2} = I_{C2} = 0$
5	0	0.2	$\frac{5-0.2}{1K} = 4.8mA$	$I_{B1} = \frac{5-0.7}{20K} = 0.215mA$ $I_{C1} = I_R = 4.8mA$	$I_{B2} = I_{C2} = 0$
0	5	0.2	4.8mA	$I_{B1} = I_{C1} = 0$	$I_{B2} = 0.215mA$ $I_{C2} = 4.8mA$
5	5	0.2	4.8mA	$I_{B1} = 0.215mA$ $I_{C1} = I_{C2}/2 = 2.4mA$	$I_{B2} = 0.215mA$ $I_{C2} = I_R/2 = 2.4mA$

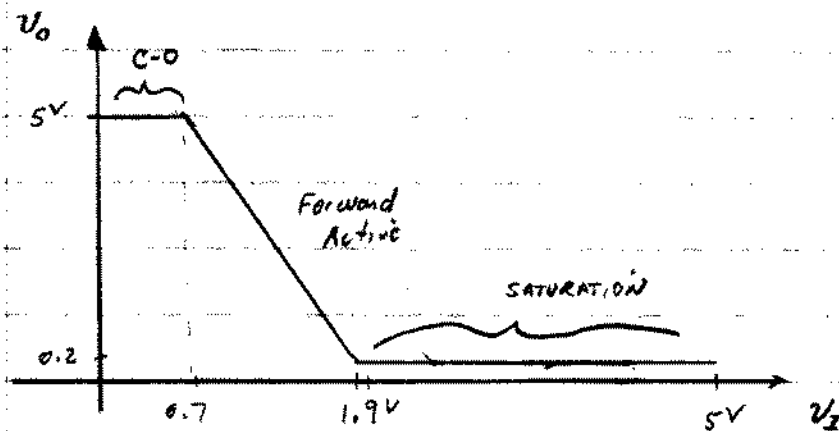
C. Amplifier

$$\beta_F = 100$$

$$V_A = \infty$$

$$V_{BE(on)} = 0.7$$

$$V_{CE(sat)} = 0.2$$

Sketch Transfer Characteristic (V_O vs. V_I)

For $V_I < 0.7V$, Q is C-O ($V_O = 5V$)

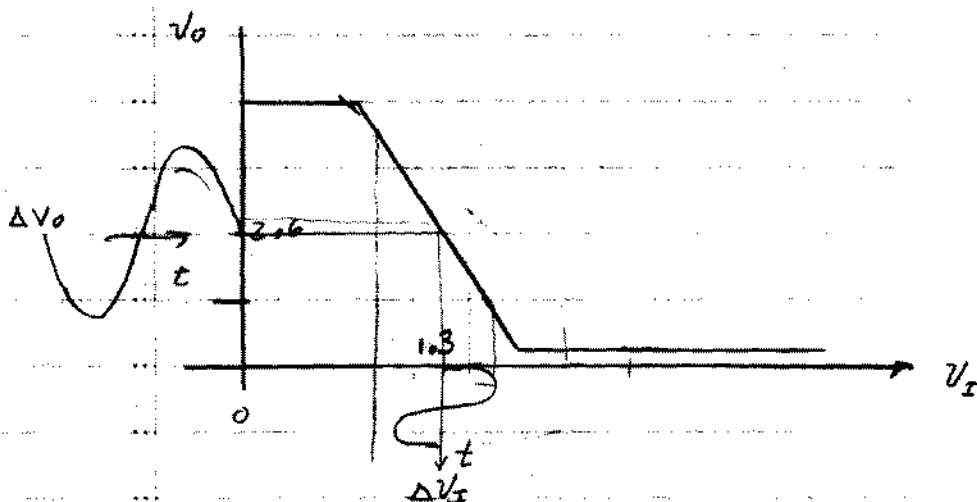
For $V_I > 0.7$, Q is ON
$$I_B = \frac{V_I - V_{BE(on)}}{R_E} = \frac{V_I - 0.7}{100k}$$

$$V_O = V^+ - \beta I_B R_C = 5 - 100 \left[\frac{V_I - 0.7}{100k} \right] 4k = 5 - 4(V_I - 0.7)$$

at $V_I > 1.9$ $V_O = 0.2$ in SAT

AC Analysis

- Set $V_I = 1.3V = V_{BB}$ and input an AC source ΔV_I .



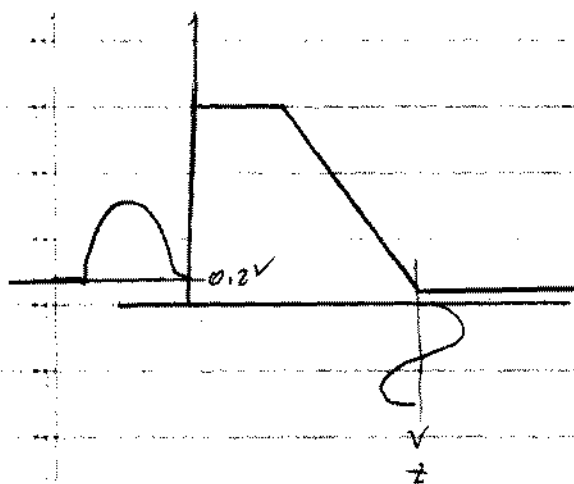
Note:
$$I_B = \frac{V_{BB} + \Delta V_I - V_{BE(on)}}{R_B} = \frac{(1.3 - 0.7) + \Delta V_I}{100k\Omega}$$

$$V_O = V^+ - \beta I_B R_C = 5 - (100) \left[\frac{0.6 + \Delta V_I}{100k} \right] 4k$$

$$\boxed{V_O = 2.6 - 4\Delta V_I}$$

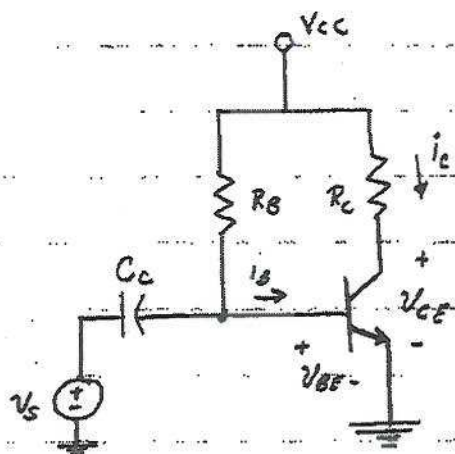
$$\text{Gain} = A_V = \frac{\Delta V_O}{\Delta V_I} = \boxed{-4}$$

Suppose $V_I = 1.9V$



B. Single Base Resistor Biasing

1.



DC ANALYSIS

INPUT CIRCUIT

$$KVL: I_{BQ} = \frac{V_{CC} - V_{BE}}{R_B}$$

OUTPUT CIRCUIT

$$KVL: I_{CQ} = \frac{V_{CC} - V_{CEQ}}{R_C}$$

Ex. 10.12 Consider $V_{CC} = 12V$, $V_{BE(on)} = 0.7V$, $R_C = 6k\Omega$, $R_B = 1.13M\Omega$.

then for $\beta_F = 100$:

$$I_{BQ} = \frac{V_{CC} - V_{BE(on)}}{R_B} = \frac{12 - 0.7}{1.13M} = 10\mu A$$

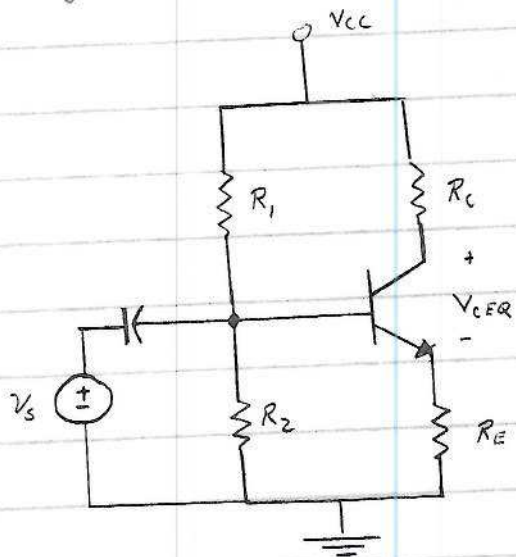
$$V_{CEQ} = V_{CC} - \beta_F I_B R_C = 12 - (100)(10\mu A)(6k) = \underline{6V}$$

for $\beta_F = 50$:

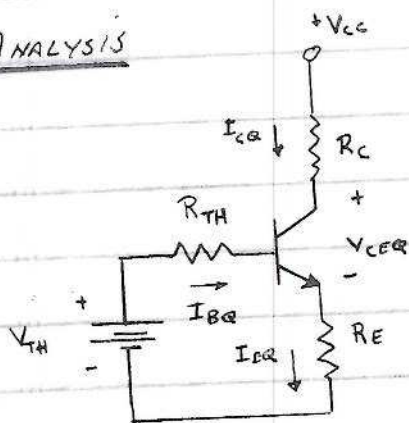
$$V_{CEQ} = 12 - (50)(10\mu A)(6k) = \underline{9V}$$

50% $\downarrow \beta_F$, 50% $\uparrow V_{CEQ}$

C. Voltage Divider Biasing & the Emitter Resistor



ANALYSIS



WHERE: $V_{TH} = \frac{R_2}{R_1 + R_2} V_{CC}$

$R_{TH} = R_1 // R_2 = \frac{R_1 R_2}{R_1 + R_2}$

Now: $V_{CEQ} = V_{CC} - \beta_F I_{BQ} R_C - (\beta_F + 1) I_{BQ} R_E$

However: KVL: $-V_{TH} + I_{BQ} R_{TH} + V_{BE} + (\beta_F + 1) I_{BQ} R_E = 0$

So $I_{BQ} = \frac{V_{TH} - V_{BE}}{R_{TH} + (\beta_F + 1) R_E}$

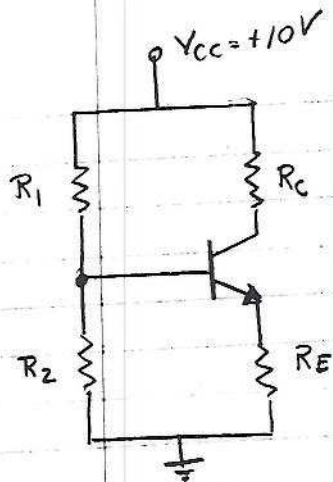
$\therefore V_{CE} = V_{CC} - \left[\frac{V_{TH} - V_{BE}}{R_{TH} + (\beta_F + 1) R_E} \right] \left[\beta_F R_C + (\beta_F + 1) R_E \right]$

NEARLY
INDEPENDENT
OF
 β

If by design $R_{TH} \ll (\beta_F + 1) R_E$;

then $V_{CEQ} \approx V_{CC} - \left[\frac{V_{TH} - V_{BE}}{(\beta_F + 1) R_E} \right] \left[\frac{\beta_F R_C}{(\beta_F + 1) R_E} + 1 \right]$

Ex.



Given: $\beta = 100$, $V_{BE,ON} = 0.7V$
 $R_1 = 56k\Omega$

$R_2 = 12.2k\Omega$

$R_C = 2k\Omega$

$R_E = 0.4k\Omega$

Find the Qpt: I_{CQ} & V_{CEQ}

① $R_{TH} = R_1 \parallel R_2 = 56k \parallel 12.2k = 10k\Omega$

$V_{TH} = \left(\frac{R_2}{R_1 + R_2} \right) 10V = \frac{12.2}{12.2 + 56} (10) = 1.79V$

② $-V_{TH} + I_B R_{TH} + V_{BE,ON} + I_E R_E = 0$

$I_B = \frac{V_{TH} - V_{BE,ON}}{R_{TH} + (\beta + 1) R_E} = \frac{1.79 - 0.7}{10k + (101)(0.4k)} = 21.6\mu A$

③ $I_{CQ} = \beta I_B = 2.16mA$

④ $V_{CEQ} = V_{CC} - I_{CQ} R_C - I_{EQ} R_E$

$= 10 - (2.16k) 2^{mA} - (101)(21.6\mu A)(0.4k)$
 $= 4.81V$

b) $\beta = 50$?

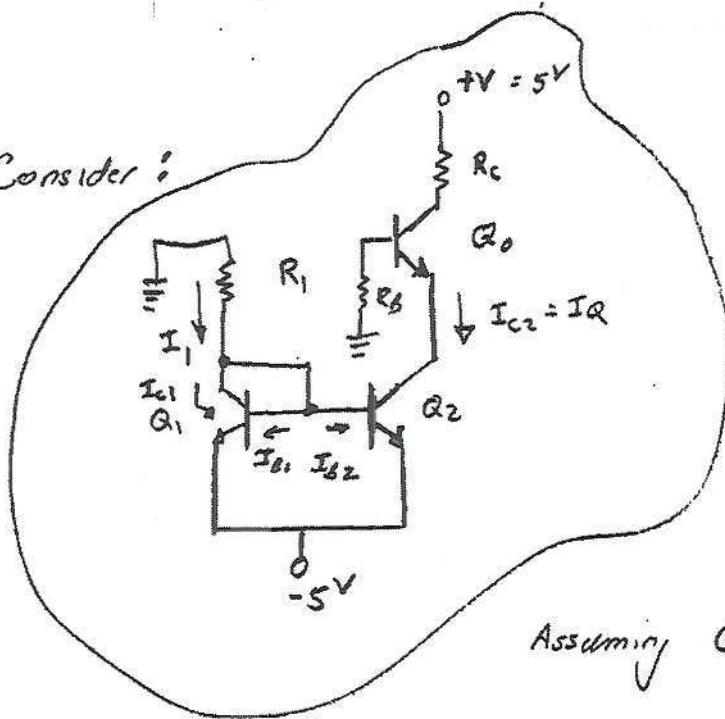
$I_B = \frac{1.79 - 0.7}{10k + (51)(0.4k)} = 36\mu A$

$I_{CQ} = (50)(36\mu A) = 1.80mA$

$V_{CEQ} = V_{CC} - I_{CQ} R_C - I_{EQ} R_E$
 $= 10 - 1.8(2) - (51)(36\mu A)(0.4k)$
 $= 5.67V$

D. Integrated Circuit Biasing

Consider:



R_1 - Q_1 Loop

$$0 = I_1 R_1 + V_{BE(ON)} + V^-$$

$$I_1 = \frac{-(V^- + V_{BE(ON)})}{R_1}$$

ALSO

$$I_1 = I_{C1} + I_{B1} + I_{B2}$$

Assuming Q_1 & Q_2 are identical:

$$I_1 = I_{C1} + 2I_{B2} = I_{C2} \left(1 + \frac{2}{\beta}\right)$$

$$I_{C2} = I_Q = \frac{I_1}{1 + \frac{2}{\beta}}$$

Ex. Let $R_1 = 10k\Omega$, $\beta = 50$, $V_{BE(ON)} = 0.7V$

Then

$$I_1 = \frac{-(V^- + V_{BE(ON)})}{R_1} = \frac{-(-5 + 0.7)}{10k} = 0.43mA$$

$$I_{C2} = \left(\frac{I_1}{1 + \frac{2}{\beta}}\right) = \frac{0.43mA}{(1 + \frac{2}{50})} = 0.413mA$$

$$I_{B1} = I_{B2} = \frac{I_{C2}}{\beta} = \frac{0.413}{50} = 8.26\mu A$$